

IN THE CLAIMS

Claims 1-14 are amended as follows:

Sub 1
B1

1. (Once Amended) A semiconductor device comprising:
a substrate;
a protruding portion which is formed on the top face of the substrate and the top of which serves as a dummy element for controlling a chemical mechanical polishing process;
and
a conductive layer which is formed on the substrate so as to have a spiral shape and which serves as an induction element,
wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

2. (Once Amended) A semiconductor device as set forth in claim 1, wherein the substrate is an SOI substrate, and
said protruding portion is formed of an SOI layer of said SOI substrate.

3. (Once Amended) A semiconductor device as set forth in claim 2, wherein the substrate includes an N-type semiconductor layer.

4. (Once Amended) A semiconductor device as set forth in claim 2, wherein the substrate includes a P-type semiconductor layer.

Sub 2

5. (Once Amended) A semiconductor device comprising:
a substrate;
a protruding portion which is formed on the top face of the substrate and the top of which serves as a dummy element for controlling a chemical mechanical polishing process;
a conductive layer which is formed on the substrate so as to have a spiral shape and which serves as an induction element; and

Sub 2 > a protective film which is formed between the substrate and said conductive layer and prevents silicidation of said protruding portion.

6. (Once Amended) A semiconductor device as set forth in claim 5, wherein the substrate is an SOI substrate, and said protruding portion is formed of an SOI layer of said SOI substrate.

Sub 3 > 7. (Once Amended) A semiconductor device as set forth in claim 6, which further comprises an extracting wiring which is connected to said conductive layer.

Q 8. (Once Amended) A semiconductor device as set forth in claim 6, wherein the substrate includes an N-type semiconductor layer.

9. (Once Amended) A semiconductor device as set forth in claim 6, wherein the substrate includes a P-type semiconductor layer.

Sub B2 > 10. (Once Amended) A semiconductor device as set forth in claim 5, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

11. (Once Amended) A semiconductor device as set forth in claim 10, wherein the substrate is an SOI substrate, and said protruding portion is formed of an SOI layer of said SOI substrate.

Sub 4 > 12. (Once Amended) A semiconductor device as set forth in claim 11, which further comprises an extracting wiring which is connected to said conductive layer.

13. (Once Amended) A semiconductor device as set forth in claim 11, wherein the substrate includes an N-type semiconductor layer.

14. (Once Amended) A semiconductor device as set forth in claim 11, wherein the substrate includes a P-type semiconductor layer.